

What is claimed is:

1. A method of fabricating an optical semiconductor device, comprising the steps of:

    forming a plurality of optical semiconductor elements on a semiconductor substrate;

    forming a dummy portion in a center of a square at four corners of which said optical semiconductor elements are arranged; and

    forming a buried layer by vapor phase epitaxy so as to bury a portion between said optical semiconductor elements and said dummy portion.

2. A method according to claim 1, wherein said buried layer is formed by vapor phase epitaxy using one of a chloride-based source gas and a hydride-based source gas.